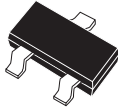


CMPT4033

PNP SILICON TRANSISTOR



SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPT4033 type is an PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for very high current, general purpose amplifier applications.

Marking Code is C4A.

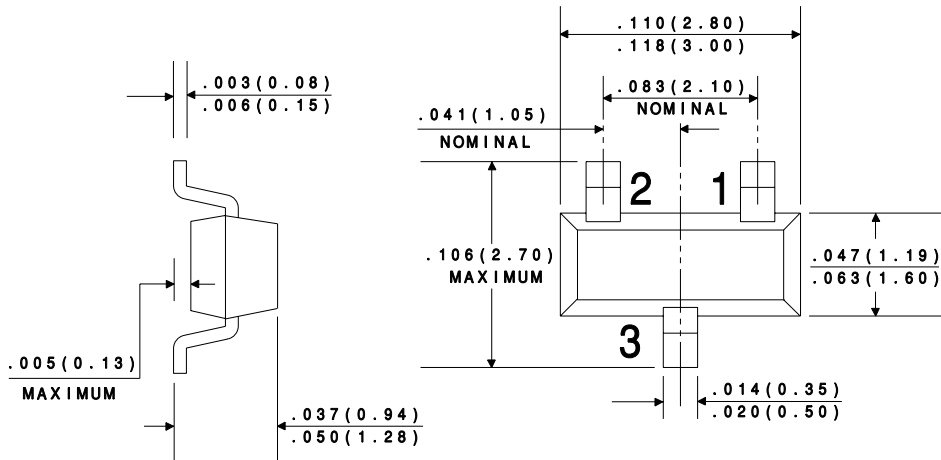
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	500	mA
Collector Current (Peak)	I _{CM}	1.0	A
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =60V		50	nA
I _{EBO}	V _{EB} =5.0V		10	nA
BV _{CBO}	I _C =10μA	80		V
BV _{CEO}	I _C =10mA	80		V
BV _{EBO}	I _E =10μA	5.0		V
V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.15	V
V _{CE(SAT)}	I _C =500mA, I _B =50mA		0.50	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA		0.90	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA		1.10	V
h _{FE}	V _{CE} =5.0V, I _C =0.1mA	75		
h _{FE}	V _{CE} =5.0V, I _C =100mA	100	300	
h _{FE}	V _{CE} =5.0V, I _C =500mA	70		
f _T	V _{CE} =10V, I _C =50mA, f=1.0MHz	100		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		20	pF
C _{ib}	V _{EB} =0.5V, I _C =0, f=1.0MHz		110	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.